



General Description

FSMOS[®] MOSFET is based on Oriental Semiconductor's unique device design to achieve low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The high V_{th} series is specially designed to use in motor control systems with driving voltage of more than 10V.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery



Applications

- PD charger
- Motor driver
- Switching voltage regulator
- DC-DC convertor
- Switching mode power supply

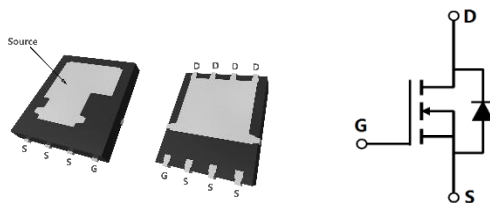
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	80	V
I_D , pulse	800	A
$R_{DS(ON)}$, max @ $V_{GS}=10V$	2.3	$m\Omega$
Q_g	58.5	nC

Marking Information

Product Name	Package	Marking
SFS08R023UGSCNF	DSCPPAK5×6	08R023

Package & Pin information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	80	V
Gate-source voltage	V_{GS}	± 20	V
Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_D	370	A
Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{D, \text{pulse}}$	800	A
Continuous diode forward current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_S	370	A
Diode pulsed current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{S, \text{pulse}}$	800	A
Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$	P_D	600	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	951	mJ
Operation and storage temperature	T_{stg}, T_j	-55 to 175	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction - case, bottom	$R_{\theta JC}$	0.25	$^{\circ}\text{C/W}$
Thermal resistance, junction - case, top	$R_{\theta JC}$	1.8	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	50	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	80			V	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	2		4	V	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$
Drain-source on-state resistance	$R_{DS(ON)}$		1.7	2.3	$\text{m}\Omega$	$V_{GS}=10\text{ V}, I_D=50\text{ A}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=20\text{ V}$
				-100		$V_{GS}=-20\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=80\text{ V}, V_{GS}=0\text{ V}$
Gate resistance	R_G		1.8		Ω	$f=1\text{ MHz}$, Open drain

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		4195		pF	$V_{GS}=0\text{ V}$, $V_{DS}=40\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		1295		pF	
Reverse transfer capacitance	C_{rss}		45.5		pF	
Turn-on delay time	$t_{d(on)}$		18		ns	$V_{GS}=10\text{ V}$, $V_{DS}=40\text{ V}$, $R_G=2\ \Omega$, $I_D=50\text{ A}$
Rise time	t_r		12		ns	
Turn-off delay time	$t_{d(off)}$		33.2		ns	
Fall time	t_f		13		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		58.5		nC	$V_{GS}=10\text{ V}$, $V_{DS}=40\text{ V}$, $I_D=50\text{ A}$
Gate-source charge	Q_{gs}		16.4		nC	
Gate-drain charge	Q_{gd}		12.1		nC	
Gate plateau voltage	$V_{plateau}$		4.3		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	$I_S=50\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		35.2		ns	$V_R=40\text{ V}$, $I_S=50\text{ A}$, $di/dt=400\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		85		nC	
Peak reverse recovery current	I_{rrm}		4.3		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^{\circ}\text{C}$.
- 5) $V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $L=0.3\text{ mH}$, starting $T_j=25\text{ }^{\circ}\text{C}$.

Electrical Characteristics Diagrams

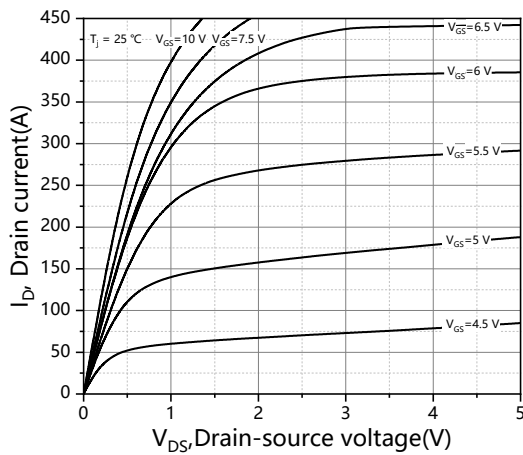


Figure 1. Typ. output characteristics

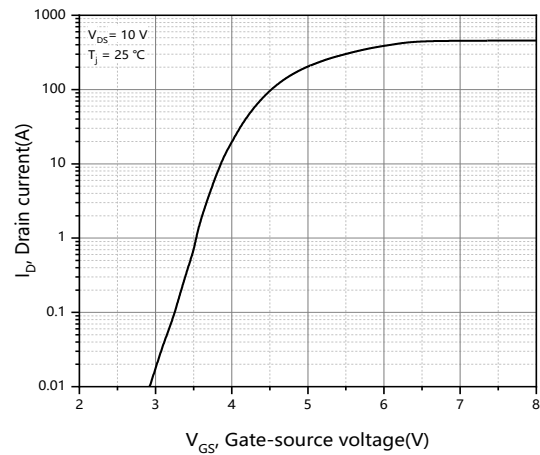


Figure 2. Typ. transfer characteristics

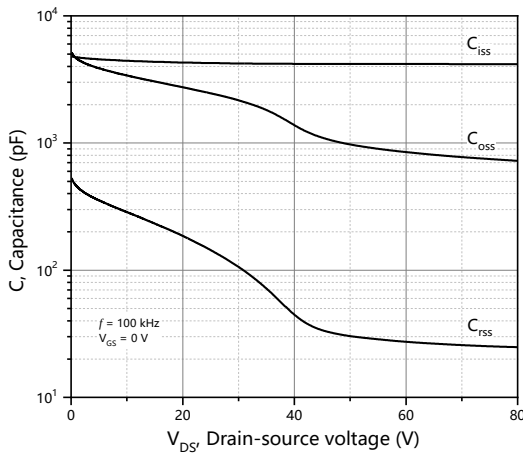


Figure 3. Typ. capacitances

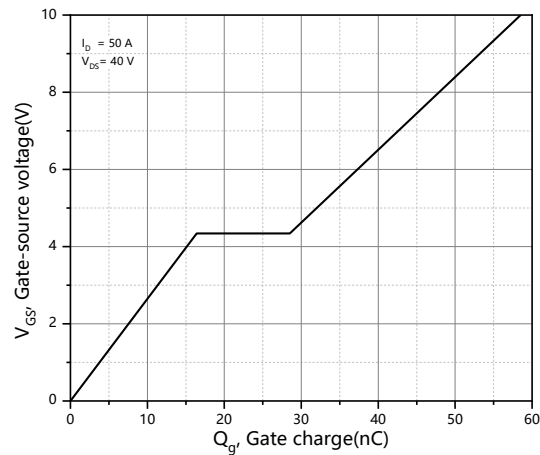


Figure 4. Typ. gate charge

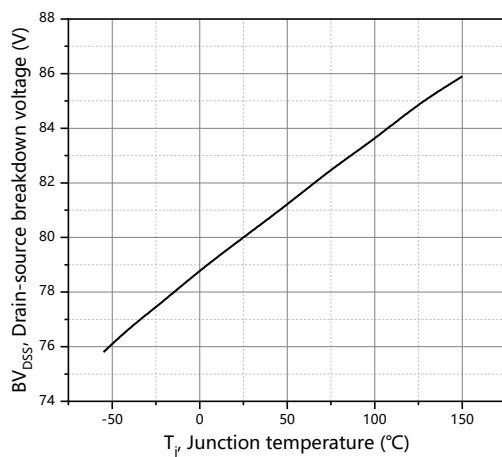


Figure 5. Drain-source breakdown voltage

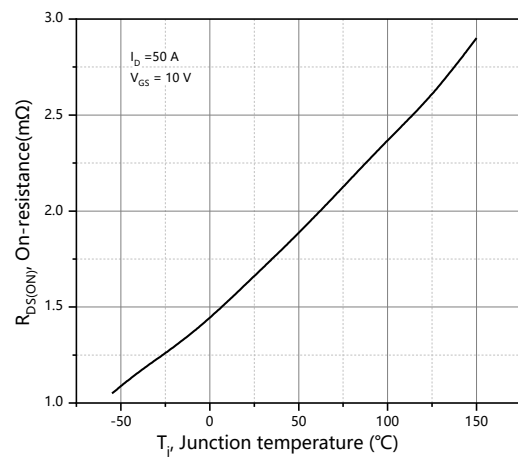


Figure 6. Drain-source on-state resistance

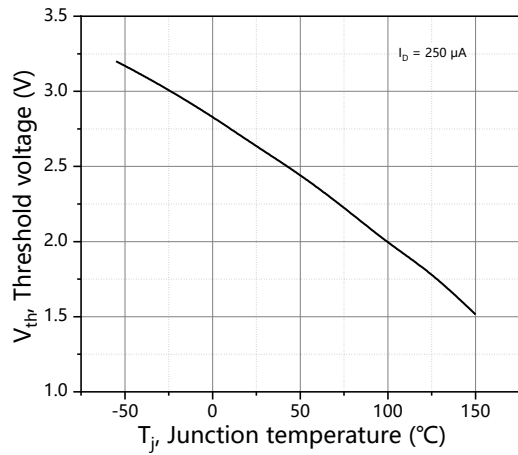


Figure 7. Threshold voltage

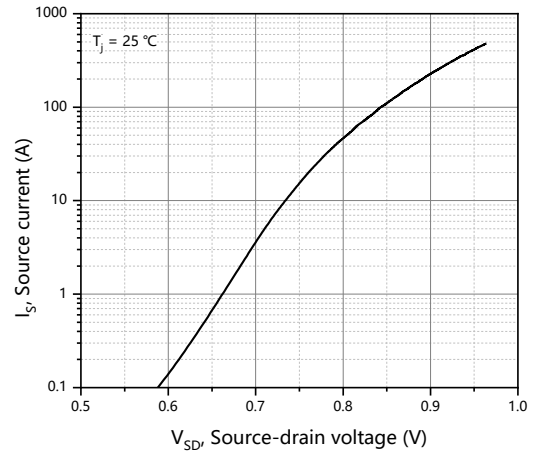


Figure 8. Forward characteristic of body diode

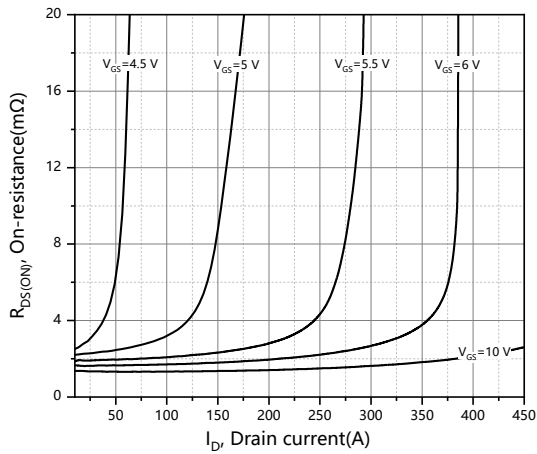


Figure 9. Drain-source on-state resistance

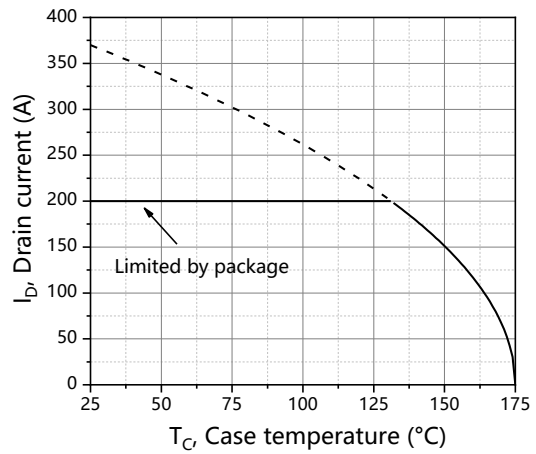


Figure 10. Drain current

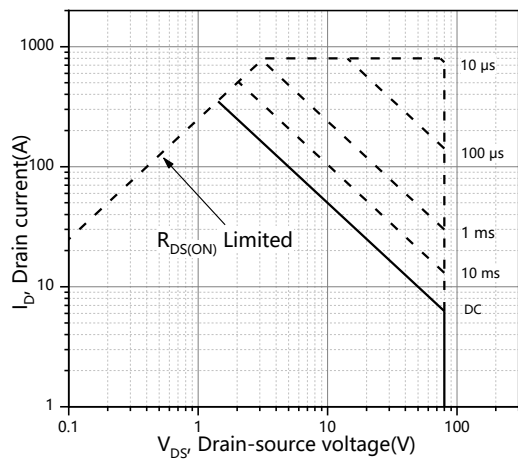


Figure 11. Safe operation area $T_C=25^{\circ}\text{C}$

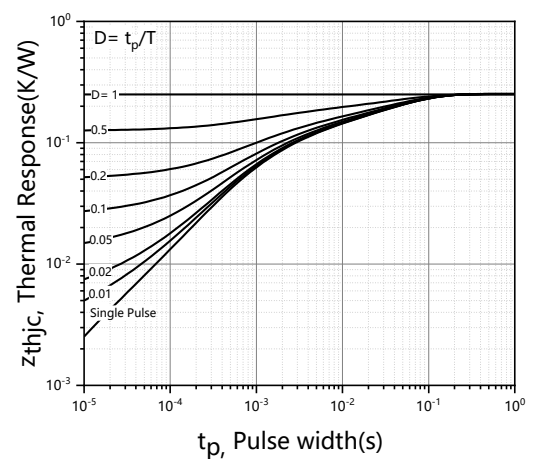


Figure 12. Max. transient thermal impedance

Test circuits and waveforms

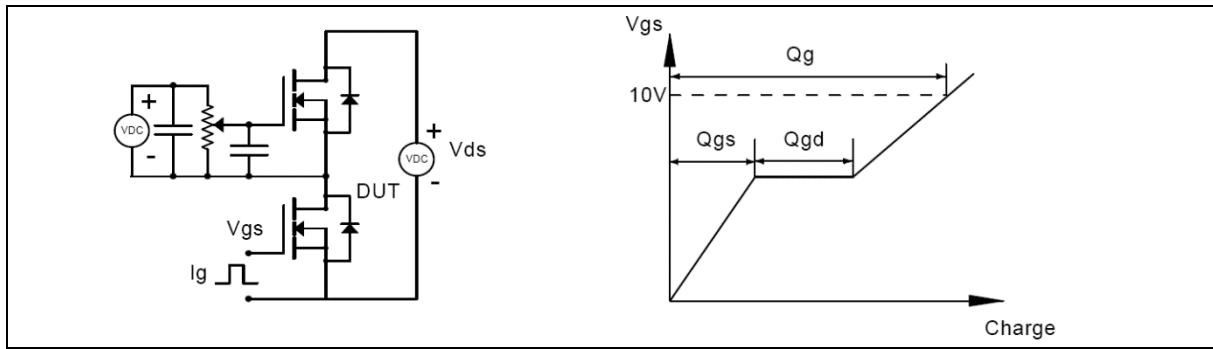


Figure 1. Gate charge test circuit & waveform

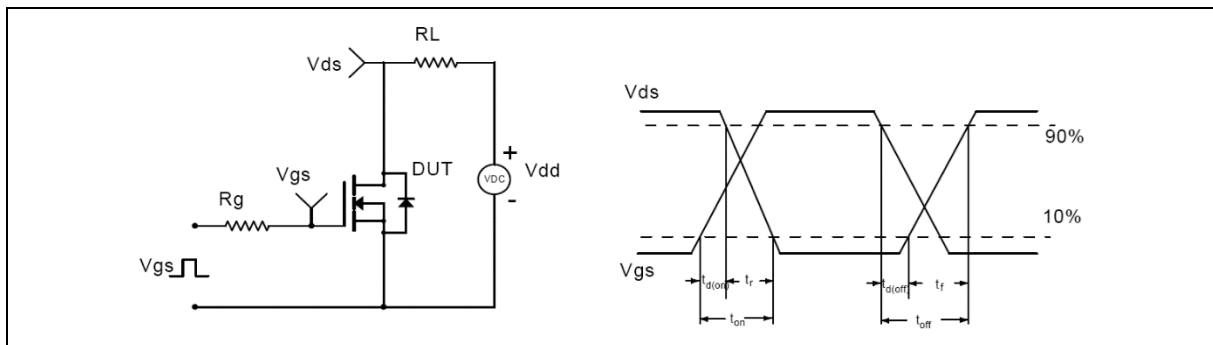


Figure 2. Switching time test circuit & waveforms

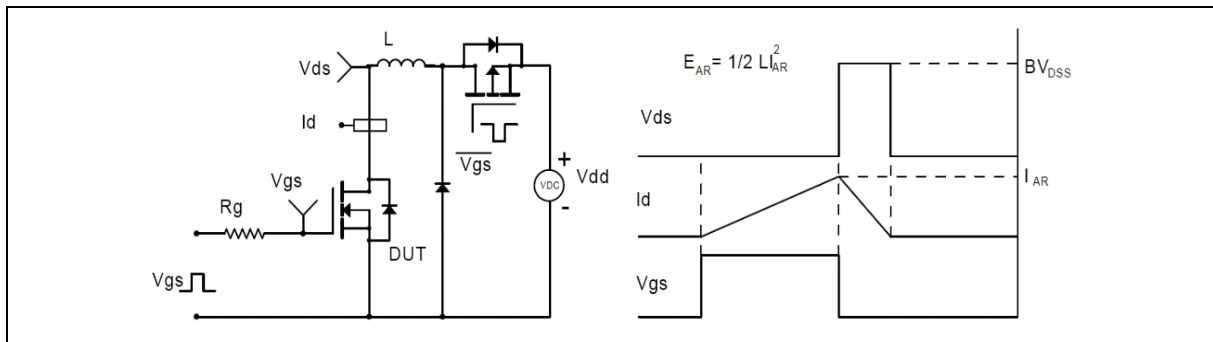


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

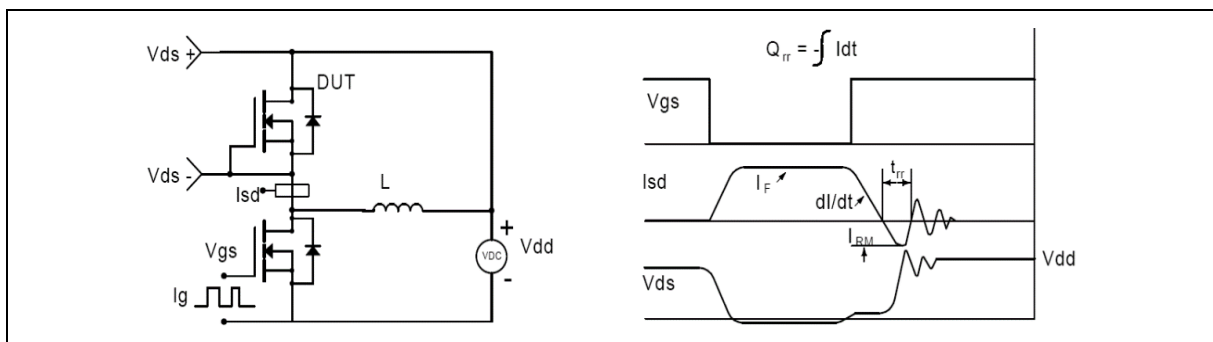
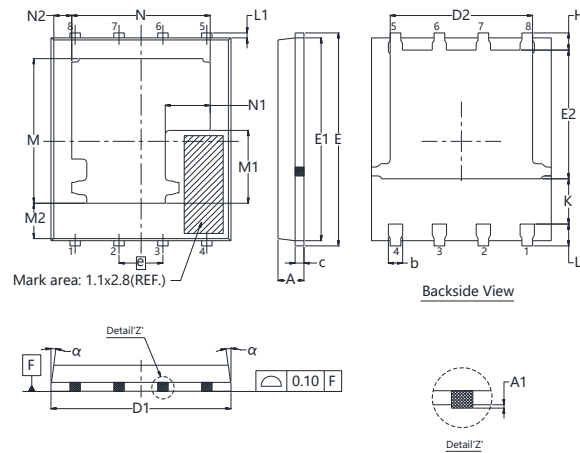


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	0.65	0.75	0.85
A1	0.00	-	0.05
b	0.33	0.40	0.50
c	0.200	0.250	0.300
D1	5.00	5.20	5.40
D2	3.80	4.10	4.25
E	6.00	6.15	6.30
E1	5.760	5.860	5.960
E2	3.520	3.720	3.920
e	1.27BSC		
H	0.40	0.50	0.60
K	1.10	-	-
L	0.50	0.60	0.70
L1	0.08	0.15	0.22
a	0°	-	12°
M	4.18 REF		
M1	2.10REF		
M2	1.00 REF		
N	4.00 REF		
N1	1.30REF		
N2	0.50 REF		

Version : DSCPPAK5×6-M package outline dimension

Ordering Information

Package Type	Units/ Reel	Reels / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
DSCPPAK5×6-M	5000	2	10000	6	60000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFS08R023UGSCNF	DSCPPAK5×6	yes	yes	yes

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Revision History

Version	Revision History	Date
V1.0	Initial release	2025-09-29